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Electric-field tunable electronic structure in WSe<sub>2</sub>/arsenene van der Waals heterostructure

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## **Highlights**

- · It is demonstrated that the WSe<sub>2</sub>/arsenene heterobilayer is a type-II vdW heterostructure, and thus electrons and holes are spatially separated.
- The WSe<sub>2</sub>/arsenene heterobilayer undergoes a transition from semiconductor to metal when subjected to an external electric field.
- The positive and negative external electric field have different effects on the band gap due to the spontaneous electric polarization in  $WSe_2/arsenene$  heterostructure.
- The WSe<sub>2</sub>/arsenene vdW heterostructure experiences transitions from type-II to type-I and then from type-I to type-II under various external electric fields.

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